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6_27_07.1 - Actual Results

Substrate: F-A9858 gb
As Temp: 363
As Set: 7e-6
Comments: C. Marcus repeat of 2-25-05.1

label	relay	rate	temp	set pt
Al8	1	0.4066	1055.000	18.860
Ga5	3	1.2559	945.000	944.000

Layer#	Layer Type	Thickness	Time	Total Time	Al8	Sub (V)	Si (A)	C (A)
1	chgSi chgC As11	0.00	60.00	60.00	---	25.911	0.001	0.007
2	Ga5As11	7000.00	5573.69	5633.69	---	25.909	0.002	0.006
3	PauseAs11	0.00	3600.00	9233.69	---	25.910	0.002	0.007
4*	Al8Ga5As11	100.00	60.15	9293.84	0.245	25.914	0.002	0.003
5*	Ga5As11	30.00	23.89	9317.73	---	25.911	0.002	0.004
6* (100)	PauseAs11	0.00	15.00	9332.73	---	25.915	0.002	0.006
304	Al8Ga5As11	3000.00	1804.51	20941.97	0.245	25.910	0.003	0.006
305	Al8As11	19.81	48.72	20990.69	---	25.913	0.003	0.006
306	Ga5As11	5.66	4.51	20995.19	---	25.913	0.002	0.006
307	t-627.9	0.00	10.00	21005.19	---	25.910	0.004	0.006
308	chgTemp As11	0.00	90.00	21095.19	---	0.018	0.003	0.006
309	chgTemp As11	0.00	2.00	21097.19	---	17.107	0.003	0.006
310	chgSi As11	0.00	15.00	21112.19	---	17.103	7.413	0.006
311	SiAs11	0.00	28.00	21140.19	---	17.103	7.413	0.008
312	chgSi As11	0.00	10.00	21150.19	---	17.101	0.000	0.007
313	Ga5As11	22.64	18.03	21168.22	---	17.104	0.002	0.008
314	t-455.2	0.00	10.00	21178.22	---	17.104	0.003	0.009
315	chgTemp As11	0.00	85.00	21263.22	---	32.168	0.002	0.007
316	startTempAs11	0.00	2.00	21265.22	---	25.911	0.002	0.007
317	Al8As11	19.81	48.72	21313.94	---	25.910	0.002	0.004
318	Al8Ga5As11	800.00	481.20	21795.15	0.245	25.913	0.006	0.006
319	PauseAs11	0.00	50.00	21845.15	---	25.911	0.002	0.006
320	Ga5As11	300.00	238.87	22084.02	---	25.914	0.003	0.008
321	t-621.0	0.00	10.00	22094.02	---	25.914	0.004	0.008
322	PauseAs11	0.00	40.00	22134.02	---	25.913	0.003	0.007
323	Al8Ga5As11	800.00	481.20	22615.22	0.245	25.913	0.002	0.006
324	Al8As11	19.81	48.72	22663.94	---	25.913	0.001	0.007
325	Ga5As11	5.66	4.51	22668.45	---	25.910	0.002	0.007
326	chgTemp As11	0.00	90.00	22758.45	---	0.014	0.001	0.006
327	chgTemp As11	0.00	2.00	22760.45	---	17.106	0.002	0.006
328	chgSi As11	0.00	15.00	22775.45	---	17.104	7.410	0.007
329	SiAs11	0.00	55.00	22830.45	---	17.104	7.410	0.007
330	chgSi As11	0.00	10.00	22840.45	---	17.104	0.000	0.008
331	Ga5As11	22.64	18.03	22858.48	---	17.104	0.002	0.006
332	t-458.6	0.00	10.00	22868.48	---	17.105	0.002	0.003
333	chgTemp As11	0.00	85.00	22953.48	---	32.168	0.002	0.006
334	startTempAs11	0.00	2.00	22955.48	---	25.914	0.002	0.007
335	Al8As11	19.81	48.72	23004.20	---	25.914	0.002	0.007
336	Al8Ga5As11	980.00	589.47	23593.67	0.245	25.916	0.002	0.007
337	Ga5As11	100.00	79.62	23673.29	---	25.915	0.002	0.006
338	t-625.2	0.00	10.00	23683.29	---	25.915	0.002	0.004
339	chgTemp As11	0.00	2.00	23685.29	---	15.086	0.002	0.006
340	chgSi chgC As11	0.00	60.00	23745.29	---	15.083	0.389	0.395
341	BeepAs11	0.00	10.00	23755.29	---	---	---	---

total layers: 341
total time: 23755.29 sec.
total thickness: 26115.8 A.

6-27-07.1.sum.txt

SAMPLE: 6-27-07.1 STRUCTURE: 2Dx1 MEASURED: 7/10/2007 2:16 PM
POSITION: A DARK CONTACTS: flats MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 298.7 Ro: 1.9042E+3 Rh: 9.3614E+6 M: 4.9162E+3 D: 6.6764E+11
T: 77.0 Ro: 8.8045E+1 Rh: 1.6536E+7 M: 1.8781E+5 D: 3.7797E+11
T: 3.8 Ro: 2.3205E+0 Rh: 2.2644E+7 M: 9.7585E+6 D: 2.7601E+11
AFTER LIGHT
T: 3.8 Ro: 2.5535E+0 Rh: 2.1752E+7 M: 8.5183E+6 D: 2.8734E+11

7_28_08.2 - Actual Results

Substrate: F-B7111
As Temp: 289
As Set: 9.5e-6
Comments:
Einstein quiet & gatable

label	relay	rate	temp	set pt
Ga7	2	2.7928	869.000	869.000
Ga5	3	1.8377	965.000	964.000
Al4	5	0.8956	63.000	962.000

Layer#	Layer Type	Thickness	Time	Total Time	Al4	Sub (V)	Si (A)	C (A)
1	chgSi chgC As10	0.00	60.00	60.00	---	24.897	0.002	0.007
2*	Ga7As10	500.00	179.03	239.03	---	24.897	0.002	0.006
3* (10)	PauseAs10	0.00	50.00	289.03	---	24.898	0.002	0.007
22*	Ga5As10	30.00	16.32	2366.64	---	24.898	0.000	0.007
23*	PauseAs10	0.00	10.00	2376.64	---	24.901	0.000	0.008
24* (100)	Ga5Al4As10	100.00	36.59	2413.23	0.328	24.900	0.001	0.008
322	t-645.7	0.00	10.00	8651.37	---	24.898	0.000	0.007
323	Ga5Al4As10	2500.00	914.65	9566.02	0.328	24.900	0.001	0.006
324	chgTemp As10	0.00	110.00	9676.02	---	0.012	0.000	0.008
325	chgTemp As10	0.00	2.00	9678.02	---	14.568	0.000	0.007
326	chgSi As10	0.00	15.00	9693.02	---	14.568	6.908	0.009
327	SiAs10	0.00	25.00	9718.02	---	14.570	6.910	0.007
328	chgSi As10	0.00	10.00	9728.02	---	14.572	0.000	0.008
329	Ga5Al4As10	14.00	5.12	9733.14	0.328	14.570	0.000	0.008
330	t-447.2	0.00	10.00	9743.14	---	14.570	0.000	0.006
331	chgTemp As10	0.00	85.00	9828.14	---	29.127	0.001	0.008
332	startTempAs10	0.00	2.00	9830.14	---	24.896	0.002	0.007
333	t-648.6	0.00	10.00	9840.14	---	24.897	0.001	0.008
334	Ga5Al4As10	1600.00	585.37	10425.51	0.328	24.900	0.000	0.006
335	Ga7Al4As10	1400.00	379.57	10805.08	0.243	24.900	0.000	0.008
336	Ga7As10	480.00	171.87	10976.95	---	24.903	0.001	0.008
337	PauseAs10	0.00	100.00	11076.95	---	24.901	0.001	0.009
338	Ga7Al4As10	1400.00	379.57	11456.52	0.243	24.902	0.000	0.008
339	Ga5Al4As10	1600.00	585.37	12041.90	0.328	24.903	0.002	0.006
340	chgTemp As10	0.00	110.00	12151.90	---	0.015	0.000	0.008
341	chgTemp As10	0.00	2.00	12153.90	---	14.572	0.001	0.007
342	chgSi As10	0.00	15.00	12168.90	---	14.571	6.907	0.006
343	SiAs10	0.00	60.00	12228.90	---	14.572	6.909	0.006
344	chgSi As10	0.00	10.00	12238.90	---	14.573	0.000	0.006
345	Ga5Al4As10	14.00	5.12	12244.02	0.328	14.570	0.000	0.008
346	t-447.6	0.00	10.00	12254.02	---	14.571	0.001	0.007
347	chgTemp As10	0.00	85.00	12339.02	---	29.128	0.002	0.007
348	startTempAs10	0.00	2.00	12341.02	---	24.898	0.001	0.006
349	Ga5Al4As10	866.00	316.83	12657.85	0.328	24.901	0.001	0.006
350	Ga5As10	100.00	54.42	12712.27	---	24.901	0.001	0.006
351	t-640.4	0.00	10.00	12722.27	---	24.902	0.001	0.004
352	chgTemp As10	0.00	2.00	12724.27	---	8.063	0.002	0.006
353	chgSi chgC As10	0.00	60.00	12784.27	---	8.060	0.389	0.396
354	BeepAs10	0.00	10.00	12794.27	---	8.060	0.390	0.395

total layers: 354
total time: 12794.27 sec.
total thickness: 27974.0 A.

SAMPLE: 7-28-08.2 STRUCTURE: 2Dx1 MEASURED: 7/29/2008 5:33 PM
POSITION: B DARK CONTACTS: corners MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0

T: 302.4	Ro: 7.5642E+3	Rh:	4.6879E+7	M:	6.1975E+3	D:	1.3332E+11
T: 77.0	Ro: 3.9666E+2	Rh:	7.3621E+7	M:	1.8560E+5	D:	8.4895E+10
T: 3.8	Ro: 1.6277E+1	Rh:	8.1042E+7	M:	4.9789E+6	D:	7.7121E+10
AFTER LIGHT							
T: 3.8	Ro: 7.5684E+0	Rh:	4.9906E+7	M:	6.5940E+6	D:	1.2524E+11

13.4M 1.24"

Nice no // cond.

11_18_08.1 - Actual Results

Substrate: F-B7246 B3
As Temp: 289
As Set: 9.5e-6
Comments: Einstein quiet & gatable
For Jim Eisenstein

label	relay	rate	temp	set pt
Ga7	2	2.8187	878.000	877.500
Ga5	3	1.8668	970.000	969.000
Al4	5	0.8944	971.000	970.000

Layer#	Layer Type	Thickness	Time	Total Time	Al4	Sub (V)	Si (A)	C (A)
1	chgSi chgC As10	0.00	60.00	60.00	---	28.114	0.003	0.008
2*	Ga7As10	500.00	177.39	237.39	---	28.109	0.003	0.009
3* (10)	PauseAs10	0.00	50.00	287.39	---	28.106	0.004	0.010
22*	Ga5As10	30.00	16.07	2349.94	---	28.109	0.002	0.009
23*	PauseAs10	0.00	10.00	2359.94	---	28.106	0.002	0.008
24* (100)	Ga5Al4As10	100.00	36.22	2396.15	0.324	28.106	0.002	0.008
322	t-652.0	0.00	10.00	8572.51	---	28.105	0.003	0.008
323	Ga5Al4As10	2500.00	905.40	9477.91	0.324	28.108	0.002	0.010
324	chgTemp As10	0.00	110.00	9587.91	---	0.010	0.002	0.011
325	chgTemp As10	0.00	2.00	9589.91	---	14.564	0.002	0.010
326	chgSi As10	0.00	15.00	9604.91	---	14.564	6.913	0.011
327	SiAs10	0.00	25.00	9629.91	---	14.566	6.913	0.009
328	chgSi As10	0.00	10.00	9639.91	---	14.566	0.000	0.010
329	Ga5Al4As10	14.00	5.07	9644.98	0.324	14.564	0.002	0.010
330	t-430.3	0.00	10.00	9654.98	---	14.563	0.002	0.008
331	chgTemp As10	0.00	85.00	9739.98	---	29.843	0.002	0.009
332	startTempAs10	0.00	2.00	9741.98	---	28.103	0.002	0.010
333	PauseAs10	0.00	120.00	9861.98	---	28.104	0.002	0.009
334	t-642.1	0.00	10.00	9871.98	---	28.108	0.002	0.010
335	Ga5Al4As10	600.00	217.30	10089.28	0.324	28.110	0.002	0.008
336	Ga7Al4As10	700.00	188.52	10277.80	0.241	28.110	0.002	0.008
337	Ga7As10	300.00	106.43	10384.23	---	28.108	0.002	0.007
338	PauseAs10	0.00	100.00	10484.23	---	28.105	0.002	0.010
339	Ga7Al4As10	700.00	188.52	10672.76	0.241	28.108	0.002	0.011
340	Ga5Al4As10	600.00	217.30	10890.05	0.324	28.109	0.003	0.010
341	chgTemp As10	0.00	110.00	11000.05	---	0.010	0.002	0.009
342	chgTemp As10	0.00	2.00	11002.05	---	14.567	0.003	0.009
343	chgSi As10	0.00	15.00	11017.05	---	14.566	6.913	0.009
344	SiAs10	0.00	60.00	11077.05	---	14.563	6.913	0.009
345	chgSi As10	0.00	10.00	11087.05	---	14.563	0.000	0.010
346	Ga5Al4As10	14.00	5.07	11092.12	0.324	14.564	0.004	0.009
347	t-428.4	0.00	10.00	11102.12	---	14.564	0.002	0.011
348	chgTemp As10	0.00	85.00	11187.12	---	29.843	0.006	0.010
349	startTempAs10	0.00	2.00	11189.12	---	28.104	0.006	0.010
350	PauseAs10	0.00	120.00	11309.12	---	28.104	0.003	0.008
351	Ga5Al4As10	866.00	313.63	11622.75	0.324	28.109	0.002	0.009
352	Ga5As10	100.00	53.57	11676.32	---	28.105	0.002	0.008
353	t-650.6	0.00	10.00	11686.32	---	28.106	0.004	0.009
354	chgTemp As10	0.00	2.00	11688.32	---	8.059	0.004	0.010
355	chgSi chgC As10	0.00	60.00	11748.32	---	8.059	0.392	0.399
356	BeepAs10	0.00	10.00	11758.32	---	8.057	0.392	0.399

EISENSTEIN

total layers: 356
total time: 11758.32 sec.
total thickness: 24394.0 A.

SAMPLE: 11-18-08.1 STRUCTURE: 2Dx1 MEASURED: 11/24/2008 1:42 PM
POSITION: A DARK CONTACTS: corners MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 297.2 Ro: 3.5573E+3 Rh: 2.6179E+7 M: 7.3591E+3 D: 2.3874E+11
T: 77.5 Ro: 1.6486E+2 Rh: 3.5620E+7 M: 2.1607E+5 D: 1.7546E+11
T: 3.8 Ro: 3.3998E+0 Rh: 4.0316E+7 M: 1.1858E+7 D: 1.5502E+11
AFTER LIGHT
T: 3.8 Ro: 2.5385E+0 Rh: 2.2876E+7 M: 9.0115E+6 D: 2.7321E+11

17.8M 2.32"

2_22_10.1 - Actual Results

Substrate: WT 19614 #47 block III
As Temp: 292
As Set: 7.9e-6
Comments: Gervais Sample

label	relay	rate	temp	set pt
Al8	1	0.8978	1003.000	17.870
Ga7	2	2.8187	928.000	928.500

Layer#	Layer Type	Thickness	Time	Total Time	Al8	Sub (V)	Si (A)	C (A)
1	chgSi chgC As10	0.00	60.00	60.00	---	28.127	0.001	0.011
2	Ga7As10	7000.00	2483.41	2543.41	---	28.126	0.002	0.008
3	PauseAs10	0.00	3000.00	5543.41	---	28.127	0.002	0.008
4*	Al8Ga7As10	100.00	26.91	5570.32	0.242	28.123	0.002	0.007
5*	Ga7As10	30.00	10.64	5580.96	---	28.122	0.002	0.008
6* (100)	PauseAs10	0.00	15.00	5595.96	---	28.124	0.002	0.009
304	Al8Ga7As10	2500.00	672.68	11471.11	0.242	28.118	0.002	0.011
305	t-641.5	0.00	10.00	11481.11	---	28.117	0.002	0.012
306	Al8As10	19.81	22.07	11503.18	---	28.120	0.003	0.011
307	Ga7As10	5.66	2.01	11505.19	---	28.120	0.003	0.010
308	chgTemp As10	0.00	120.00	11625.19	---	0.014	0.002	0.011
309	chgTemp As10	0.00	2.00	11627.19	---	18.100	0.002	0.010
310	chgSi As10	0.00	15.00	11642.19	---	18.091	7.413	0.010
311	SiAs10	0.00	17.00	11659.19	---	18.091	7.415	0.010
312	chgSi As10	0.00	10.00	11669.19	---	18.091	0.000	0.011
313	Ga7As10	22.64	8.03	11677.22	---	18.091	0.002	0.011
314	t-448.0	0.00	10.00	11687.22	---	18.092	0.003	0.010
315	chgTemp As10	0.00	107.00	11794.22	---	32.155	0.002	0.012
316	startTempAs10	0.00	2.00	11796.22	---	28.118	0.002	0.012
317	Al8As10	19.80	22.05	11818.27	---	28.116	0.002	0.012
318	Al8Ga7As10	1600.00	430.51	12248.79	0.242	28.121	0.001	0.010
319	Ga7As10	400.00	141.91	12390.70	---	28.120	0.002	0.010
320	Al8Ga7As10	1600.00	430.51	12821.21	0.242	28.118	0.002	0.011
321	t-639.5	0.00	10.00	12831.21	---	28.122	0.002	0.010
322	Al8As10	19.81	22.07	12853.27	---	28.121	0.002	0.012
323	PauseAs10	0.00	10.00	12863.27	---	28.121	0.001	0.011
324	Ga7As10	5.66	2.01	12865.28	---	28.122	0.002	0.010
325	chgTemp As10	0.00	120.00	12985.28	---	0.013	0.001	0.011
326	chgTemp As10	0.00	2.00	12987.28	---	18.091	0.002	0.011
327	chgSi As10	0.00	15.00	13002.28	---	18.092	7.414	0.010
328	SiAs10	0.00	33.00	13035.28	---	18.091	7.413	0.011
329	chgSi As10	0.00	10.00	13045.28	---	18.093	0.000	0.011
330	Ga7As10	22.64	8.03	13053.31	---	18.093	0.000	0.010
331	t-448.1	0.00	10.00	13063.31	---	18.091	0.001	0.011
332	chgTemp As10	0.00	107.00	13170.31	---	32.152	0.001	0.013
333	startTempAs10	0.00	2.00	13172.31	---	28.115	0.002	0.013
334	Al8As10	19.81	22.07	13194.38	---	28.115	0.001	0.011
335	Al8Ga7As10	980.00	263.69	13458.07	0.242	28.120	0.002	0.009
336	Ga7As10	100.00	35.48	13493.54	---	28.120	0.002	0.012
337	t-636.5	0.00	10.00	13503.54	---	28.118	0.002	0.011
338	chgSi chgC As10	0.00	60.00	13563.54	---	28.118	0.390	0.400
339	chgTemp As10	0.00	2.00	13565.54	---	10.066	0.390	0.400
340	BeepAs10		10.00	13575.54	---	10.071	0.392	0.400

total layers: 340
total time: 13575.54 sec.
total thickness: 27315.8 A.

SAMPLE: 2-22-10.1 STRUCTURE: 2Dx1 MEASURED: 2/23/2010 5:57 PM
POSITION: A DARK CONTACTS: flats MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 304.5 Ro: 3.0177E+3 Rh: 1.1382E+7 M: 3.7718E+3 D: 5.4911E+11
T: 77.3 Ro: 1.6457E+2 Rh: 2.7751E+7 M: 1.6863E+5 D: 2.2522E+11
T: 4.0 Ro: 5.7146E+0 Rh: 4.1194E+7 M: 7.2086E+6 D: 1.5172E+11

SAMPLE: 2-22-10.1 STRUCTURE: 2Dx1 MEASURED: 2/23/2010 6:12 PM
POSITION: A DARK CONTACTS: corners MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 3.8 Ro: 4.7320E+0 Rh: 4.0761E+7 M: 8.6138E+6 D: 1.5333E+11
AFTER LIGHT
T: 3.8 Ro: 4.4069E+0 Rh: 3.8673E+7 M: 8.7755E+6 D: 1.6161E+11

SAMPLE: 2-22-10.1 STRUCTURE: 2Dx1 MEASURED: 2/23/2010 6:18 PM
POSITION: A AFTER LIGHT CONTACTS: flats MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 3.8 Ro: 5.3585E+0 Rh: 3.7894E+7 M: 7.0717E+6 D: 1.6493E+11

see fractions To 8/15 18.7M 1.61"

less than usual Si in doping wells may help "switchyness"

2_23_10.1 - Actual Results
Substrate: WT 19614 #49 block VI
As Temp: 292
As Set: 7.8e-6
Comments: Angela less Si

label	relay	rate	temp	set pt
Al8	1	0.9036	1005.000	17.900
Ga7	2	2.8187	929.000	929.000

Layer#	Layer Type	Thickness	Time	Total Time	Al8	Sub (V)	Si (A)	C (A)
1	chgSi chgC As10	0.00	60.00	60.00	---	26.410	0.001	0.011
2	Ga7As10	7000.00	2483.41	2543.41	---	26.408	0.000	0.009
3	PauseAs10	0.00	3000.00	5543.41	---	26.408	0.001	0.013
4*	Al8Ga7As10	100.00	26.87	5570.28	0.243	26.407	0.001	0.013
5*	Ga7As10	30.00	10.64	5580.92	---	26.407	0.000	0.012
6* (100)	PauseAs10	0.00	15.00	5595.92	---	26.409	0.000	0.013
304	Al8Ga7As10	2500.00	671.63	11465.87	0.243	26.409	0.000	0.010
305	t-641.9	0.00	10.00	11475.87	---	26.407	0.000	0.012
306	Al8As10	19.81	21.92	11497.80	---	26.408	0.002	0.009
307	Ga7As10	5.66	2.01	11499.80	---	26.409	0.001	0.011
308	chgTemp As10	0.00	120.00	11619.80	---	0.020	0.002	0.010
309	chgTemp As10	0.00	2.00	11621.80	---	18.100	0.002	0.011
310	chgSi As10	0.00	15.00	11636.80	---	18.099	7.413	0.011
311	SiAs10	0.00	17.00	11653.80	---	18.098	7.414	0.010
312	chgSi As10	0.00	10.00	11663.80	---	18.098	0.000	0.009
313	Ga7As10	22.64	8.03	11671.84	---	18.098	0.000	0.009
314	t-445.8	0.00	10.00	11681.84	---	18.098	0.000	0.010
315	chgTemp As10	0.00	107.00	11788.84	---	32.158	0.000	0.012
316	startTempAs10	0.00	2.00	11790.84	---	26.409	0.000	0.013
317	Al8As10	19.80	21.91	11812.75	---	26.409	0.000	0.013
318	Al8Ga7As10	800.00	214.92	12027.67	0.243	26.408	0.002	0.011
319	Ga7As10	300.00	106.43	12134.10	---	26.409	0.000	0.011
320	Al8Ga7As10	800.00	214.92	12349.02	0.243	26.408	0.000	0.010
321	t-643.4	0.00	10.00	12359.02	---	26.409	0.001	0.008
322	Al8As10	19.81	21.92	12380.95	---	26.407	0.001	0.009
323	PauseAs10	0.00	10.00	12390.95	---	26.409	0.001	0.009
324	Ga7As10	5.66	2.01	12392.95	---	26.407	0.000	0.010
325	chgTemp As10	0.00	120.00	12512.95	---	0.016	0.000	0.011
326	chgTemp As10	0.00	2.00	12514.95	---	18.100	0.000	0.012
327	chgSi As10	0.00	15.00	12529.95	---	18.096	7.413	0.011
328	SiAs10	0.00	33.00	12562.95	---	18.096	7.413	0.011
329	chgSi As10	0.00	10.00	12572.95	---	18.099	0.000	0.012
330	Ga7As10	22.64	8.03	12580.99	---	18.100	0.000	0.011
331	t-454.4	0.00	10.00	12590.99	---	18.099	0.000	0.011
332	chgTemp As10	0.00	107.00	12697.99	---	32.156	0.002	0.011
333	startTempAs10	0.00	2.00	12699.99	---	26.404	0.001	0.010
334	Al8As10	19.81	21.92	12721.91	---	26.405	0.002	0.010
335	Al8Ga7As10	980.00	263.28	12985.19	0.243	26.405	0.001	0.011
336	Ga7As10	100.00	35.48	13020.67	---	26.405	0.000	0.010
337	t-638.0	0.00	10.00	13030.67	---	26.405	0.000	0.010
338	chgSi chgC As10	0.00	60.00	13090.67	---	26.404	0.388	0.401
339	chgTemp As10	0.00	2.00	13092.67	---	10.072	0.390	0.400
340	BeepAs10	0.00	10.00	13102.67	---	10.072	0.387	0.401

total layers: 340
total time: 13102.67 sec.
total thickness: 25615.8 A.

SAMPLE: 2-23-10.1 STRUCTURE: 2Dx1 MEASURED: 2/23/2010 6:38 PM
POSITION: A DARK CONTACTS: flats MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 302.1 Ro: 2.0217E+3 Rh: 1.0005E+7 M: 4.9490E+3 D: 6.2468E+11
T: 77.6 Ro: 8.5104E+1 Rh: 1.5733E+7 M: 1.8487E+5 D: 3.9725E+11
T: 3.8 Ro: 2.5562E+0 Rh: 2.2257E+7 M: 8.7074E+6 D: 2.8081E+11
AFTER LIGHT 22.3M 2.89"
T: 3.8 Ro: 2.4861E+0 Rh: 2.0541E+7 M: 8.2622E+6 D: 3.0427E+11
SAMPLE: 2-23-10.1 STRUCTURE: 2Dx1 MEASURED: 2/23/2010 6:53 PM
POSITION: A AFTER LIGHT CONTACTS: corners MANUAL CONTROL
COMMENTS:
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 3.8 Ro: 2.2137E+0 Rh: 2.0678E+7 M: 9.3406E+6 D: 3.0226E+11

25.3M 3.03"

10_12_10.1 - Actual Results

Substrate: AXT 18460 #29 block X

As Temp: 296

As Set: 8e-6

copy 8-4-10.3 = which measured 26.1 million.

Comments: Javad, Loren, shallow 3ell exact for real estate

label	relay	rate	temp	set pt
Al8	1	0.8990	1003.000	1002.000
Ga7	2	2.8357	929.000	929.000
Ga5	3	2.1183	875.000	875.000

Layer#	Layer Type	Thickness	Time	Total Time	Al8	Sub (V)	Si (A)	C (A)
1	chgSi chgC As10	0.00	60.00	60.00	---	29.664	0.003	0.013
2	Ga7As10	3000.00	1057.94	1117.94	---	29.659	0.004	0.013
3	PauseAs10	0.00	600.00	1717.94	---	29.661	0.004	0.013
4*	Ga5As10	23.00	10.86	1728.80	---	29.661	0.006	0.013
5*	PauseAs10	0.00	5.00	1733.80	---	29.658	0.004	0.013
6* (25)	Al8Ga5As10	84.90	28.14	1761.94	0.298	29.660	0.006	0.013
79	Ga5As10	23.00	10.86	2828.69	---	29.659	0.006	0.013
80	PauseAs10	0.00	600.00	3428.69	---	29.655	0.004	0.013
81*	Ga5As10	23.00	10.86	3439.54	---	29.658	0.004	0.012
82*	PauseAs10	0.00	5.00	3444.54	---	29.659	0.003	0.013
83* (25)	Al8Ga5As10	84.90	28.14	3472.68	0.298	29.658	0.004	0.013
156	Ga5As10	23.00	10.86	4539.43	---	29.658	0.004	0.013
157	PauseAs10	0.00	600.00	5139.43	---	29.656	0.004	0.013
158*	Ga5As10	23.00	10.86	5150.29	---	29.654	0.006	0.012
159*	PauseAs10	0.00	5.00	5155.29	---	29.655	0.004	0.013
160* (50)	Al8Ga5As10	84.90	28.14	5183.43	0.298	29.655	0.003	0.013
308	Al8Ga5As10	2500.00	828.56	8167.76	0.298	29.655	0.004	0.012
309	t-648.4	0.00	10.00	8177.76	---	29.656	0.006	0.013
310	Al8As10	19.81	22.04	8199.80	---	29.654	0.006	0.013
311	Ga5As10	5.66	2.67	8202.47	---	29.654	0.006	0.013
312	chgTemp As10	0.00	65.00	8267.47	---	0.026	0.003	0.012
313	chgTemp As10	0.00	2.00	8269.47	---	20.099	0.002	0.011
314	chgSi As10	0.00	15.00	8284.47	---	20.102	6.916	0.012
315	SiAs10	0.00	38.00	8322.47	---	20.103	6.916	0.012
316	chgSi As10	0.00	10.00	8332.47	---	20.101	0.000	0.012
317	Ga5As10	22.64	10.69	8343.16	---	20.102	0.006	0.012
318	t-499.1	0.00	10.00	8353.16	---	20.102	0.004	0.011
319	chgTemp As10	0.00	75.00	8428.16	---	32.176	0.004	0.011
320	startTempAs10	0.00	2.00	8430.16	---	29.652	0.003	0.011
321	Al8As10	19.81	22.04	8452.19	---	29.653	0.002	0.009
322	Al8Ga5As10	400.00	132.57	8584.76	0.298	29.653	0.006	0.011
323	t-645.6	0.00	10.00	8594.76	---	29.655	0.002	0.013
324	Al8Ga7As10	400.00	107.10	8701.86	0.241	29.654	0.002	0.013
325	Ga7As10	290.00	102.27	8804.13	---	29.654	0.002	0.011
326	Al8Ga7As10	400.00	107.10	8911.24	0.241	29.653	0.002	0.011
327	Al8Ga5As10	400.00	132.57	9043.80	0.298	29.654	0.003	0.012
328	Al8As10	19.81	22.04	9065.84	---	29.655	0.002	0.012
329	Ga5As10	5.66	2.67	9068.51	---	29.652	0.002	0.012
330	chgTemp As10	0.00	65.00	9133.51	---	0.028	0.002	0.013
331	chgTemp As10	0.00	2.00	9135.51	---	20.112	0.002	0.013
332	chgSi As10	0.00	15.00	9150.51	---	20.102	6.915	0.010
333	SiAs10	0.00	38.00	9188.51	---	20.101	6.915	0.012
334	chgSi As10	0.00	10.00	9198.51	---	20.104	0.000	0.013
335	Ga5As10	22.64	10.69	9209.20	---	20.104	0.002	0.013
336	t-500.5	0.00	10.00	9219.20	---	20.102	0.003	0.015
337	chgTemp As10	0.00	75.00	9294.20	---	32.176	0.003	0.013
338	startTempAs10	0.00	2.00	9296.20	---	29.652	0.003	0.015
339	Al8As10	19.81	22.04	9318.24	---	29.651	0.003	0.013
340	Al8Ga5As10	500.00	165.71	9483.95	0.298	29.652	0.002	0.013
341	t-644.9	0.00	10.00	9493.95	---	29.651	0.002	0.013
342	Ga5As10	5.66	2.67	9496.62	---	29.654	0.002	0.013
343	chgTemp As10	0.00	15.00	9511.62	---	0.027	0.002	0.013
344	chgTemp As10	0.00	2.00	9513.62	---	26.133	0.002	0.013
345	chgSi As10	0.00	15.00	9528.62	---	26.128	6.913	0.013
346	SiAs10	0.00	105.00	9633.62	---	26.126	6.913	0.012
347	Ga5SiAs10	5.66	2.67	9636.29	---	26.127	6.913	0.013
348	Al8Ga5As10	180.00	59.66	9695.95	0.298	26.126	6.913	0.013
349	Ga5As10	140.00	66.09	9762.04	---	26.127	6.913	0.012
350	chgSi							
351	t-595							
352	chgTe							
353	BeepA							

total layers: 353
total time: 9844.04
total thickness: 191

SAMPLE: 10-12-10.1 STRUCTURE: 2Dx1 MEASURED: 10/14/2010 2:51 PM 101
POSITION: A DARK CONTACTS: flats MANUAL CONTROL
COMMENTS: 9 min ann
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 295.9 Ro: 2.0663E+3 Rh: 1.0698E+7 M: 5.1775E+3 D: 5.8422E+11
T: 77.3 Ro: 8.8971E+1 Rh: 1.6543E+7 M: 1.8594E+5 D: 3.7780E+11
3.8 Ro: 2.5430E+0 Rh: 2.2585E+7 M: 8.8811E+6 D: 2.7674E+11
ITER LIGHT
3.8 Ro: 2.4755E+0 Rh: 2.1968E+7 M: 8.8743E+6 D: 2.8450E+11

PLE: 10-12-10.1 STRUCTURE: 2Dx1 MEASURED: 10/14/2010 3:06 PM
TION: A AFTER LIGHT CONTACTS: corners MANUAL CONTROL
NTS: 9 min ann
CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
Ro: 2.7705E+0 Rh: 2.2241E+7 M: 8.0278E+6 D: 2.8102E+11

No 2DEG 1695Å deep 2DEG: 22.1M 2.83"
no // conduction

10_12_10.2 - Actual Results

Substrate: AXT 18460 #31 BB
As Temp: 296
As Set: 7.8e-6
Comments: shallow Javad 2ell @ 2100Å deep

2095Å Deep 2DEG

label	relay	rate	temp	set pt
Al8	1	0.8990	1003.000	1002.000
Ga7	2	2.8357	929.000	929.000
Ga5	3	2.1183	875.000	875.000

Layer#	Layer Type	Thickness	Time	Total Time	Al8	Sub (V)	Si (A)	C (A)
1	chgSi chgC As10	0.00	60.00	60.00	---	22.404	0.004	0.012
2	Ga7As10	3000.00	1057.94	1117.94	---	22.405	0.003	0.013
3	PauseAs10	0.00	600.00	1717.94	---	22.405	0.002	0.015
4*	Ga5As10	23.00	10.86	1728.80	---	22.405	0.002	0.013
5*	PauseAs10	0.00	5.00	1733.80	---	22.404	0.004	0.012
6* (25)	Al8Ga5As10	84.90	28.14	1761.94	0.298	22.407	0.003	0.013
79	Ga5As10	23.00	10.86	2828.69	---	22.404	0.004	0.013
80	PauseAs10	0.00	600.00	3428.69	---	22.407	0.003	0.013
81*	Ga5As10	23.00	10.86	3439.54	---	22.405	0.002	0.015
82*	PauseAs10	0.00	5.00	3444.54	---	22.405	0.004	0.012
83* (25)	Al8Ga5As10	84.90	28.14	3472.68	0.298	22.404	0.004	0.012
156	Ga5As10	23.00	10.86	4539.43	---	22.405	0.003	0.013
157	PauseAs10	0.00	600.00	5139.43	---	22.406	0.002	0.013
158*	Ga5As10	23.00	10.86	5150.29	---	22.407	0.002	0.016
159*	PauseAs10	0.00	5.00	5155.29	---	22.409	0.003	0.015
160* (50)	Al8Ga5As10	84.90	28.14	5183.43	0.298	22.407	0.002	0.015
308	Al8Ga5As10	2500.00	828.56	8167.76	0.298	22.407	0.003	0.013
309	t-646.7	0.00	10.00	8177.76	---	22.406	0.004	0.012
310	Al8As10	19.81	22.04	8199.80	---	22.407	0.003	0.013
311	Ga5As10	5.66	2.67	8202.47	---	22.407	0.004	0.013
312	chgTemp As10	0.00	65.00	8267.47	---	0.022	0.003	0.012
313	chgTemp As10	0.00	2.00	8269.47	---	13.189	0.003	0.012
314	chgSi As10	0.00	15.00	8284.47	---	13.188	6.915	0.012
315	SiAs10	0.00	28.00	8312.47	---	13.188	6.915	0.012
316	chgSi As10	0.00	10.00	8322.47	---	13.189	0.000	0.013
317	Ga5As10	22.64	10.69	8333.16	---	13.191	0.002	0.013
318	t-485.4	0.00	10.00	8343.16	---	13.190	0.002	0.013
319	chgTemp As10	0.00	30.00	8373.16	---	32.170	0.002	0.012
320	startTempAs10	0.00	2.00	8375.16	---	22.405	0.002	0.013
321	Al8As10	19.81	22.04	8397.19	---	22.405	0.002	0.013
322	Al8Ga5As10	400.00	132.57	8529.76	0.298	22.404	0.002	0.013
323	t-643.4	0.00	10.00	8539.76	---	22.406	0.002	0.012
324	Al8Ga7As10	800.00	214.21	8753.97	0.241	22.406	0.002	0.012
325	Ga7As10	330.00	116.37	8870.34	---	22.404	0.002	0.012
326	Al8Ga7As10	800.00	214.21	9084.55	0.241	22.405	0.002	0.013
327	Al8Ga5As10	400.00	132.57	9217.12	0.298	22.406	0.003	0.013
328	Al8As10	19.81	22.04	9239.15	---	22.405	0.003	0.013
329	Ga5As10	5.66	2.67	9241.83	---	22.406	0.002	0.012
330	chgTemp As10	0.00	65.00	9306.83	---	0.025	0.002	0.013
331	chgTemp As10	0.00	2.00	9308.83	---	13.190	0.002	0.013
332	chgSi As10	0.00	15.00	9323.83	---	13.190	6.912	0.012
333	SiAs10	0.00	28.00	9351.83	---	13.190	6.913	0.013
334	chgSi As10	0.00	10.00	9361.83	---	13.190	0.000	0.013
335	Ga5As10	22.64	10.69	9372.51	---	13.191	0.002	0.013
336	t-484.0	0.00	10.00	9382.51	---	13.190	0.002	0.013
337	chgTemp As10	0.00	30.00	9412.51	---	32.173	0.002	0.013
338	startTempAs10	0.00	2.00	9414.51	---	22.402	0.002	0.012
339	Al8As10	19.81	22.04	9436.55	---	22.402	0.004	0.012
340	Al8Ga5As10	500.00	165.71	9602.26	0.298	22.405	0.003	0.012
341	Ga5As10	5.66	2.67	9604.93	---	22.410	0.004	0.012
342	chgTemp As10	0.00	15.00	9619.93	---	0.026	0.004	0.012
343	chgTemp As10	0.00	2.00	9621.93	---	19.416	0.002	0.013
344	chgSi As10	0.00	15.00	9636.93	---	19.413	6.913	0.013
345	SiAs10	0.00	105.00	9741.93	---	19.412	6.913	0.013
346	Al8Ga5As10	180.00	59.66	9801.59	0.298	19.415	6.912	0.013
347	Ga5As10	140.00	66.09	9867.68	---	19.414	6.913	0.013
348	chgSi chgC As10	0.00	60.00	9927.68	---	19.414	0.390	0.402
349	chgTemp As							
350	BeepAs10							

total layers: 350
total time: 9939.68
total thickness: 200

SAMPLE: 10-12-10.2 STRUCTURE: 2Dx1 MEASURED: 10/14/2010 2:51 PM
POSITION: B DARK CONTACTS: flats MANUAL CONTROL
COMMENTS: 9 min ann
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 296.5 Ro: 3.1249E+3 Rh: 1.6303E+7 M: 5.2172E+3 D: 3.8335E+11
T: 77.4 Ro: 1.3109E+2 Rh: 2.3987E+7 M: 1.8298E+5 D: 2.6055E+11
T: 3.8 Ro: 4.6031E+0 Rh: 3.3258E+7 M: 7.2251E+6 D: 1.8793E+11
AFTER LIGHT
T: 3.8 Ro: 4.1513E+0 Rh: 3.1829E+7 M: 7.6671E+6 D: 1.9636E+11

SAMPLE: 10-12-10.2 STRUCTURE: 2Dx1 MEASURED: 10/14/2010 3:07 PM
POSITION: B AFTER LIGHT CONTACTS: corners MANUAL CONTROL
COMMENTS: 9 min ann
SOURCE CURRENT: 10.0uA MAGNET CALIBRATION (G/A): 153.0 MAGNET CURRENT (A): 3.0
T: 3.8 Ro: 4.2524E+0 Rh: 3.2182E+7 M: 7.5678E+6 D: 1.9421E+11

7-21-10-2 was a lower version of this NICE 18.1M 1.96" 243M